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2SC5658M3T5G

NPN Silicon General Purpose Amplifier Transistor

This NPN transistor is designed for general purpose amplifier applications. This device is housed in the SOT-723 package which is designed for low power surface mount applications, where board space is at a premium.

- Reduces Board Space
- High h_{FE} , 210–460 (typical)
- Low $V_{CE(sat)}$, < 0.5 V
- ESD Performance: Human Body Model; > 2000 V, Machine Model; > 200 V
- Available in 8 mm, 7-inch/3000 Unit Tape and Reel
- This is a Pb–Free Device

MAXIMUM RATINGS ($T_A = 25^{\circ}C$)

Rating	Symbol	Value	Unit
Collector-Base Voltage	V _{(BR)CBO}	50	Vdc
Collector-Emitter Voltage	V _{(BR)CEO}	50	Vdc
Emitter-Base Voltage	V _{(BR)EBO}	5.0	Vdc
Collector Current – Continuous	Ι _C	100	mAdc

THERMAL CHARACTERISTICS

Rating	Symbol	Max	Unit
Power Dissipation (Note 1)	PD	260	mW
Junction Temperature	TJ	150	°C
Storage Temperature Range	T _{stg}	-55 ~ +150	°C

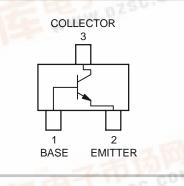
 Device mounted on a FR-4 glass epoxy printed circuit board using the minimum recommended footprint.



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NPN GENERAL PURPOSE AMPLIFIER TRANSISTORS SURFACE MOUNT





XX = Specific Device Code M = Date Code

ORDERING INFORMATION

Device	Package	Shipping [†]	
2SC5658M3T5G	SOT-723	3000/Tape & Reel	

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.



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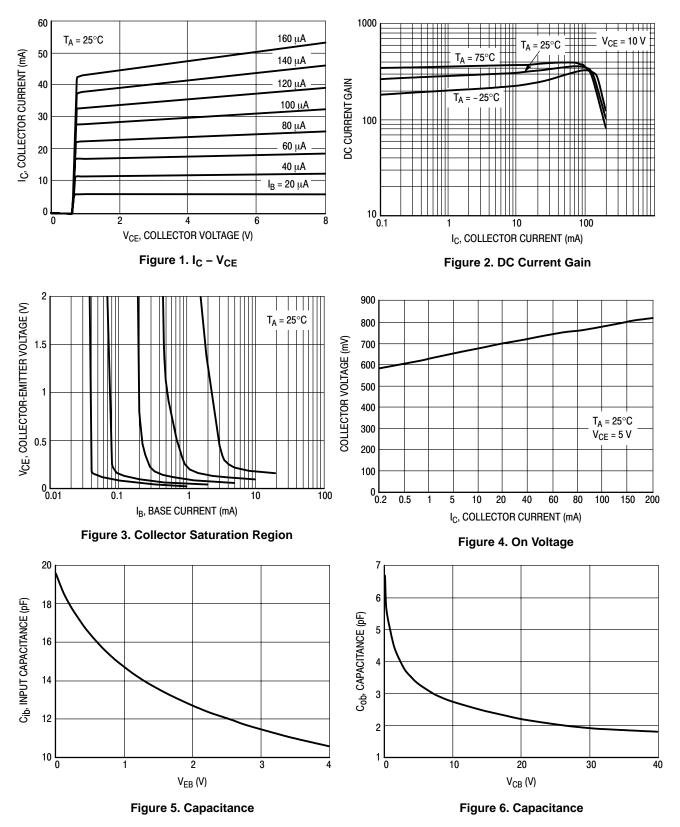
ELECTRICAL CHARACTERISTICS (T_A = 25°C)

Characteristic	Symbol	Min	Тур	Max	Unit
Collector-Base Breakdown Voltage ($I_C = 50 \ \mu Adc$, $I_E = 0$)	V _{(BR)CBO}	50	-	-	Vdc
Collector-Emitter Breakdown Voltage ($I_C = 1.0 \text{ mAdc}, I_B = 0$)	V _{(BR)CEO}	50	-	-	Vdc
Emitter-Base Breakdown Voltage ($I_E = 50 \ \mu Adc$, $I_E = 0$)	V _{(BR)EBO}	5.0	-	-	Vdc
Collector-Base Cutoff Current ($V_{CB} = 30$ Vdc, $I_E = 0$)	I _{CBO}	-	-	0.5	μΑ
Emitter-Base Cutoff Current ($V_{EB} = 4.0 \text{ Vdc}, I_B = 0$)	I _{EBO}	-	-	0.5	μΑ
Collector-Emitter Saturation Voltage (Note 2) $(I_{C} = 60 \text{ mAdc}, I_{B} = 5.0 \text{ mAdc})$	V _{CE(sat)}	-	-	0.4	Vdc
DC Current Gain (Note 2) ($V_{CE} = 6.0$ Vdc, $I_C = 1.0$ mAdc)	h _{FE}	120	-	560	-
Transition Frequency (V_{CE} = 12 Vdc, I_C = 2.0 mAdc, f = 30 MHz)	f _T	-	180	-	MHz
Output Capacitance (V_{CB} = 12 Vdc, I_C = 0 Adc, f = 1.0 MHz)	C _{OB}	-	2.0	-	pF

2. Pulse Test: Pulse Width \leq 300 $\mu s,\, D.C. \leq$ 2%.

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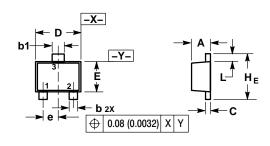
TYPICAL ELECTRICAL CHARACTERISTICS



2SC5658M3T5G

PACKAGE DIMENSIONS

SOT-723 CASE 631AA-01 **ISSUE A**

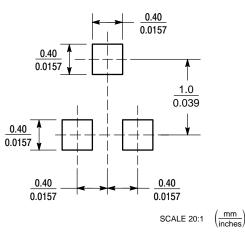


NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- Y14.5M, 1982. CONTROLLING DIMENSION: MILLIMETERS. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. 3.

	MILLIMETERS INCHES					
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.45	0.50	0.55	0.018	0.020	0.022
b	0.15	0.20	0.27	0.0059	0.0079	0.0106
b1	0.25	0.3	0.35	0.010	0.012	0.014
С	0.07	0.12	0.17	0.0028	0.0047	0.0067
D	1.15	1.20	1.25	0.045	0.047	0.049
Е	0.75	0.80	0.85	0.03	0.032	0.034
e	0.40 BSC		0.016 BSC			
ΗE	1.15	1.20	1.25	0.045	0.047	0.049
L	0.15	0.20	0.25	0.0059	0.0079	0.0098

SOLDERING FOOTPRINT*



SOT-723

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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